



INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	
				Filing Date	
				First Named Inventor	
				Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	740819-408

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US-			
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FOREIGN PATENT DOCUMENTS							
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Application of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
DV		LAI, ET AL., "A COMPARISON BETWEEN NO-ANNEALED O_2 -AND N_2O -GROWN GATE DIELECTRICS", PROCEEDINGS 1998 IEEE HONG KONG ELECTRON DEVICES MEETING, PP. 36-39, AUGUST 29, 1998, CHINA	
DV		LIN, ET AL., "LEAKAGE CURRENT, RELIABILITY CHARACTERISTICS, AND BORON PENETRATION OF ULTRA-THIN (32-36Å) O_2 -OXIDES AND N_2O/NO OXYNITRIDES", IEDM 96, PP. 331-334, 1996	
DV		SUN, ET AL., "MOS CHARACTERISTICS OF N_2O -GROWN AND NO-ANNEALED OXYNITRIDES", 4 TH INTERNATIONAL TECHNOLOGY PROCEEDINGS, PP. 90-92, NOVEMBER 1995	
DV		NOTICE OF REASONS OF REJECTION DATED DECEMBER 24, 2003	

Examiner Signature	<i>Phuland</i>	Date Considered	11/21/04
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